

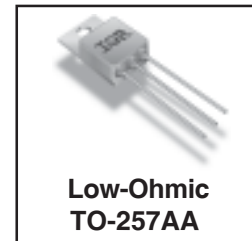
**RADIATION HARDENED
 POWER MOSFET
 THRU-HOLE (Low-Ohmic TO-257AA)**

**2N7590T3
 IRHYS67134CM
 150V, N-CANNEL**



Product Summary

Part Number	Radiation Level	R _{DS(on)}	I _D
IRHYS67134CM	100K Rads (Si)	0.090Ω	19A
IRHYS63134CM	300K Rads (Si)	0.090Ω	19A



International Rectifier's R6™ technology provides superior power MOSFETs for space applications. These devices have improved immunity to Single Event Effect (SEE) and have been characterized for useful performance with Linear Energy Transfer (LET) up to 90MeV/(mg/cm²). Their combination of very low R_{DS(on)} and faster switching times reduces power loss and increases power density in today's high speed switching applications such as DC-DC converters and motor controllers. These devices retain all of the well established advantages of MOSFETs such as voltage control, ease of paralleling and temperature stability of electrical parameters.

Features:

- Low R_{DS(on)}
- Fast Switching
- Single Event Effect (SEE) Hardened
- Low Total Gate Charge
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Ceramic Eyelets
- Electrically Isolated
- Light Weight
- ESD Rating: Class 2 per MIL-STD-750, Method 1020

Absolute Maximum Ratings

Pre-Irradiation

	Parameter		Units
I _D @ V _{GS} = 12V, T _C = 25°C	Continuous Drain Current	19	A
I _D @ V _{GS} = 12V, T _C = 100°C	Continuous Drain Current	12	
I _{DM}	Pulsed Drain Current ①	76	
P _D @ T _C = 25°C	Max. Power Dissipation	75	W
	Linear Derating Factor	0.6	W/°C
V _{GS}	Gate-to-Source Voltage	±20	V
EAS	Single Pulse Avalanche Energy ②	67	mJ
I _{AR}	Avalanche Current ①	19	A
EAR	Repetitive Avalanche Energy ①	7.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	7.8	V/ns
T _J	Operating Junction	-55 to 150	°C
T _{STG}	Storage Temperature Range		
	Lead Temperature	300 (0.063 in. /1.6 mm from case for 10s)	
	Weight	4.3 (Typical)	g

For footnotes refer to the last page

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Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
B _V DSS	Drain-to-Source Breakdown Voltage	150	—	—	V	V _{GS} = 0V, I _D = 1.0mA
ΔB _V DSS/ΔT _J	Temperature Coefficient of Breakdown Voltage	—	0.19	—	V/°C	Reference to 25°C, I _D = 1.0mA
R _{DS(on)}	Static Drain-to-Source On-State Resistance	—	—	0.090	Ω	V _{GS} = 12V, I _D = 12A ④
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 1.0mA
ΔV _{GS(th)} /ΔT _J	Gate Threshold Voltage Coefficient	—	-9.51	—	mV/°C	
g _{fs}	Forward Transconductance	14	—	—	S	V _{DS} = 15V, I _{DS} = 12A ④
I _{DSS}	Zero Gate Voltage Drain Current	—	—	10	μA	V _{DS} = 120V, V _{GS} = 0V
		—	—	25		V _{DS} = 120V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	—	-100	nA	V _{GS} = -20V
Q _g	Total Gate Charge	—	—	50	nC	V _{GS} = 12V, I _D = 19A
Q _{gs}	Gate-to-Source Charge	—	—	15		V _{DS} = 75V
Q _{gd}	Gate-to-Drain ('Miller') Charge	—	—	18		
t _{d(on)}	Turn-On Delay Time	—	—	20	ns	V _{DD} = 75V, I _D = 19A, V _{GS} = 12V, R _G = 7.5Ω
t _r	Rise Time	—	—	30		
t _{d(off)}	Turn-Off Delay Time	—	—	35		
t _f	Fall Time	—	—	25		
L _S + L _D	Total Inductance	—	6.8	—	nH	Measured from Drain lead (6mm / 0.025 in from package) to Source lead (6mm/ 0.025 in from package)
C _{iss}	Input Capacitance	—	1540	—	pF	V _{GS} = 0V, V _{DS} = 25V f = 1.0MHz
C _{oss}	Output Capacitance	—	240	—		
C _{rss}	Reverse Transfer Capacitance	—	5.2	—		
R _g	Gate Resistance	—	1.1	—	Ω	f = 1.0MHz, open drain

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	19	A	T _j = 25°C, I _S = 19A, V _{GS} = 0V ④
I _{SM}	Pulse Source Current (Body Diode) ①	—	—	76		
V _{SD}	Diode Forward Voltage	—	—	1.2	V	T _j = 25°C, I _F = 19A, di/dt ≤ 100A/μs
t _{rr}	Reverse Recovery Time	—	—	300	ns	V _{DD} ≤ 25V ④
Q _{RR}	Reverse Recovery Charge	—	—	2.6	μC	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L _S + L _D .				

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R _{thJC}	Junction-to-Case	—	—	1.67	°C/W	Typical Socket Mount
R _{thJA}	Junction-to-Ambient	—	—	80		

Note: Corresponding Spice and Saber models are available on International Rectifier Web site.

For footnotes refer to the last page

Radiation Characteristics

IRHYS67134CM, 2N7590T3

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table 1. Electrical Characteristics @ T_j = 25°C, Post Total Dose Irradiation ⑤⑥

	Parameter	Up to 300K Rads (Si) ¹		Units	Test Conditions
		Min	Max		
BV _{DSS}	Drain-to-Source Breakdown Voltage	150	—	V	V _{GS} = 0V, I _D = 1.0mA
V _{GS(th)}	Gate Threshold Voltage	2.0	4.0		V _{GS} = V _{DS} , I _D = 1.0mA
I _{GSS}	Gate-to-Source Leakage Forward	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	-100		V _{GS} = -20V
I _{DSS}	Zero Gate Voltage Drain Current	—	10	μA	V _{DS} = 120V, V _{GS} = 0V
R _{DS(on)}	Static Drain-to-Source On-State Resistance (TO-3) ④	—	0.092	Ω	V _{GS} = 12V, I _D = 12A
R _{DS(on)}	Static Drain-to-Source On-State Resistance (Low Ohmic TO-257) ④	—	0.090	Ω	V _{GS} = 12V, I _D = 12A
V _{SD}	Diode Forward Voltage ④	—	1.2	V	V _{GS} = 0V, I _D = 19A

1. Part numbers IRHYS67134CM and IRHYS63134CM

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Typical Single Event Effect Safe Operating Area

LET (MeV/(mg/cm ²))	Energy (MeV)	Range (μm)	VDS (V)				
			@VGS=0V	@VGS=-5V	@VGS=-10V	@VGS=-15V	@VGS=-20V
39 ± 5%	410 ± 5%	50 ± 5%	150	150	150	150	150
61 ± 5%	825 ± 5%	66 ± 7.5%	150	150	150	40	-
90 ± 5%	1470 ± 5%	80 ± 5%	50	50	30	-	-

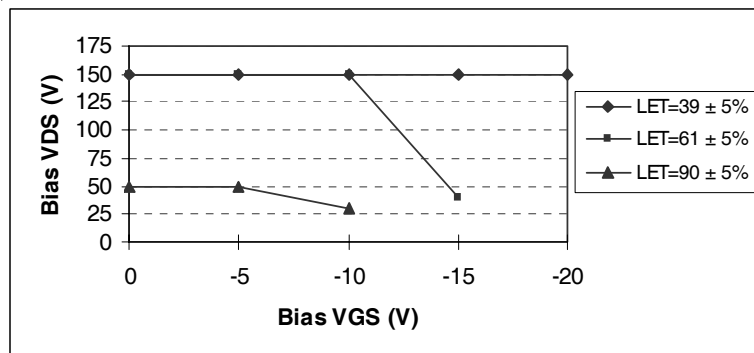


Fig a. Typical Single Event Effect, Safe Operating Area

For footnotes refer to the last page

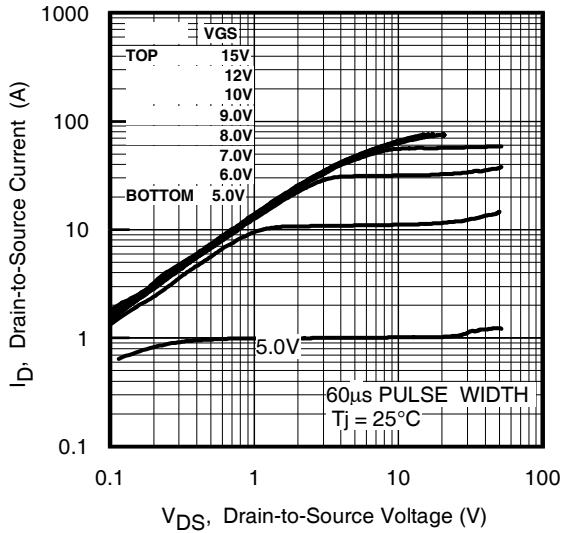


Fig 1. Typical Output Characteristics

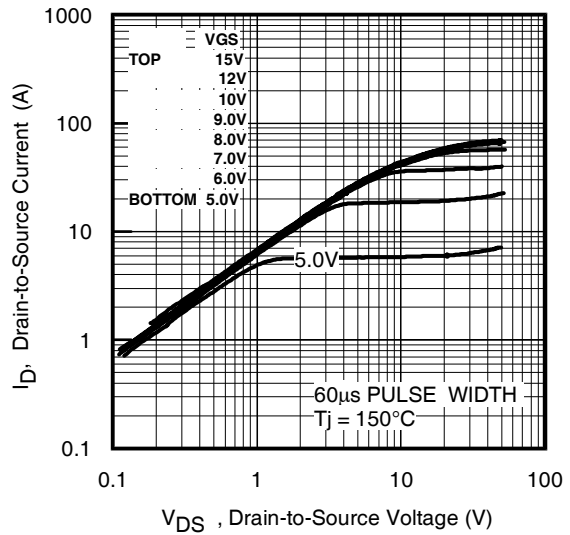


Fig 2. Typical Output Characteristics

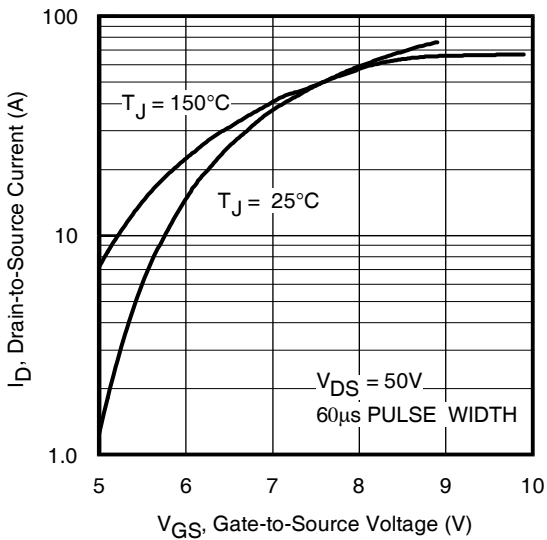


Fig 3. Typical Transfer Characteristics

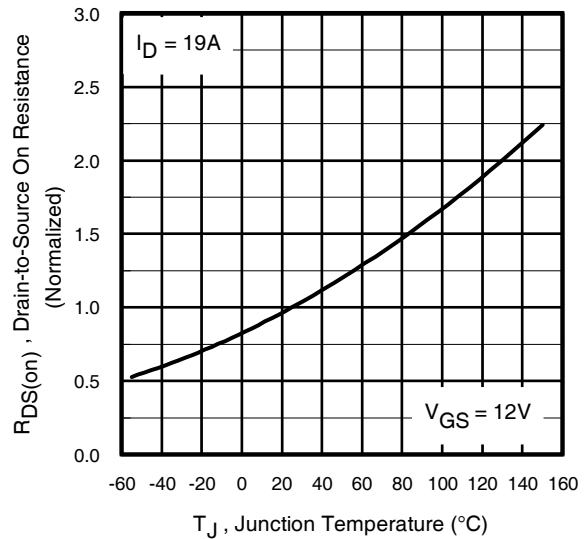


Fig 4. Normalized On-Resistance Vs. Temperature

Pre-Irradiation

IRHYS67134CM, 2N7590T3

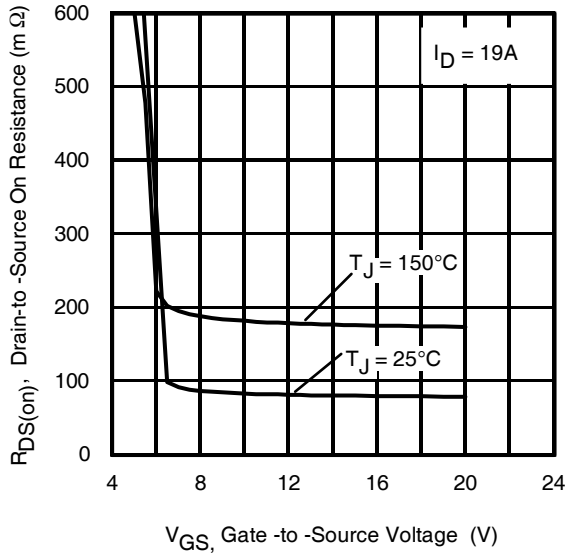


Fig 5. Typical On-Resistance Vs Gate Voltage

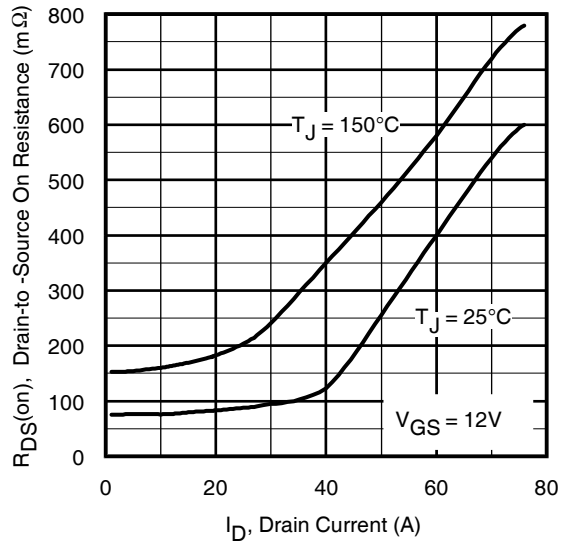


Fig 6. Typical On-Resistance Vs Drain Current

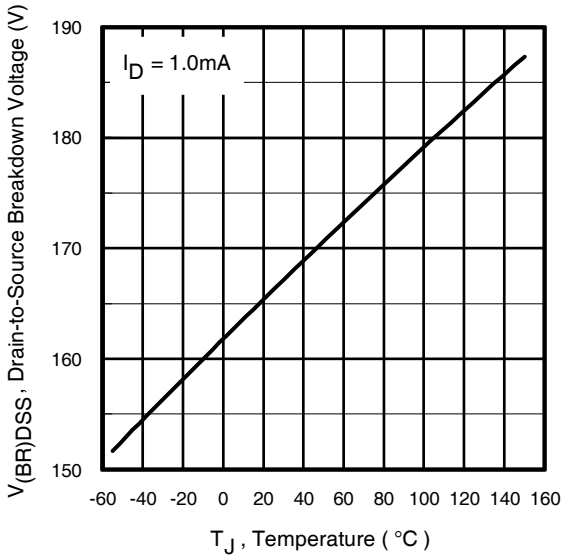


Fig 7. Typical Drain-to-Source Breakdown Voltage Vs Temperature

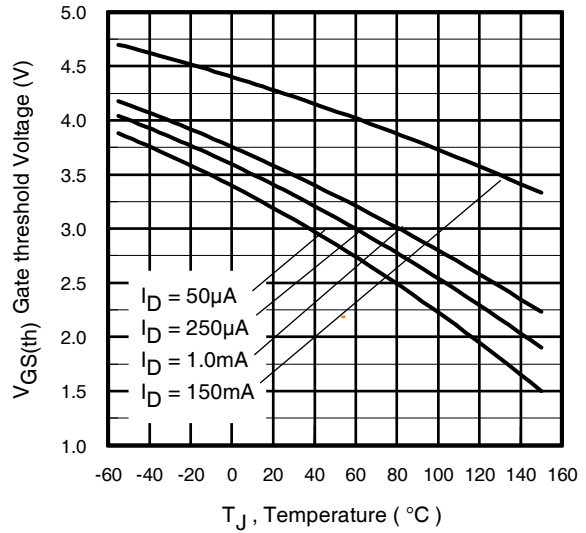


Fig 8. Typical Threshold Voltage Vs Temperature

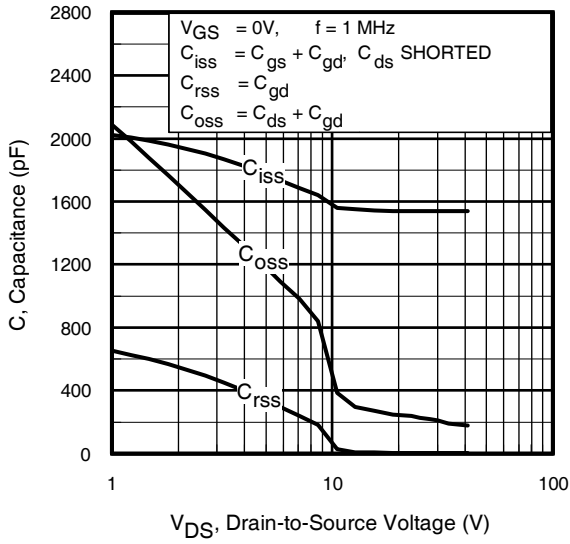


Fig 9. Typical Capacitance Vs. Drain-to-Source Voltage

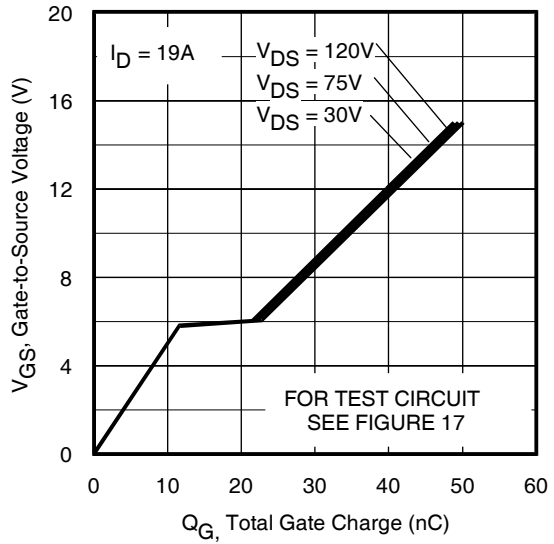


Fig 10. Typical Gate Charge Vs. Gate-to-Source Voltage

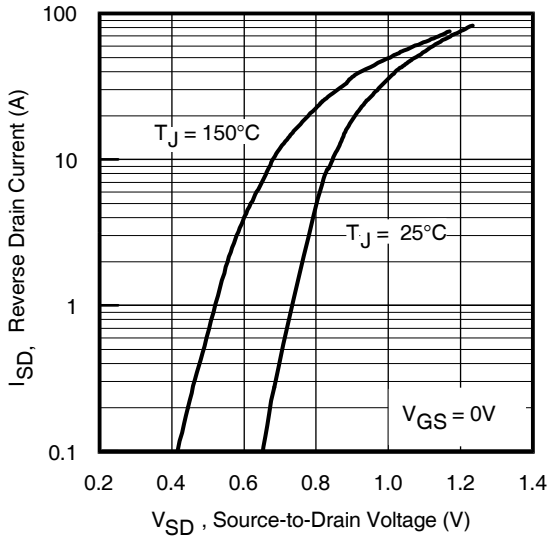


Fig 11. Typical Source-Drain Diode Forward Voltage

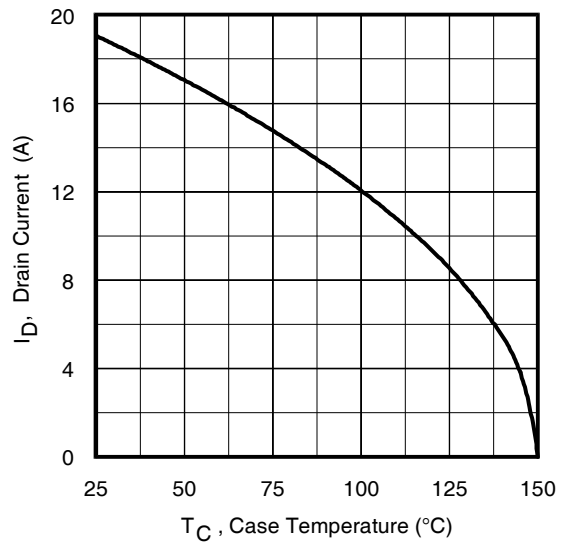


Fig 12. Maximum Drain Current Vs. Case Temperature

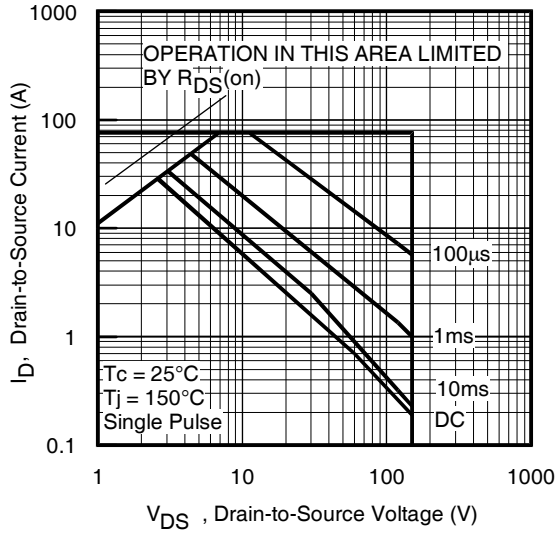


Fig 13. Maximum Safe Operating Area

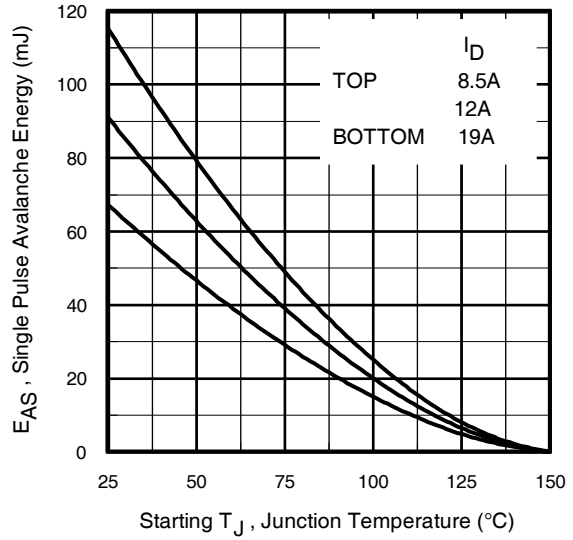


Fig 14. Maximum Avalanche Energy Vs. Drain Current

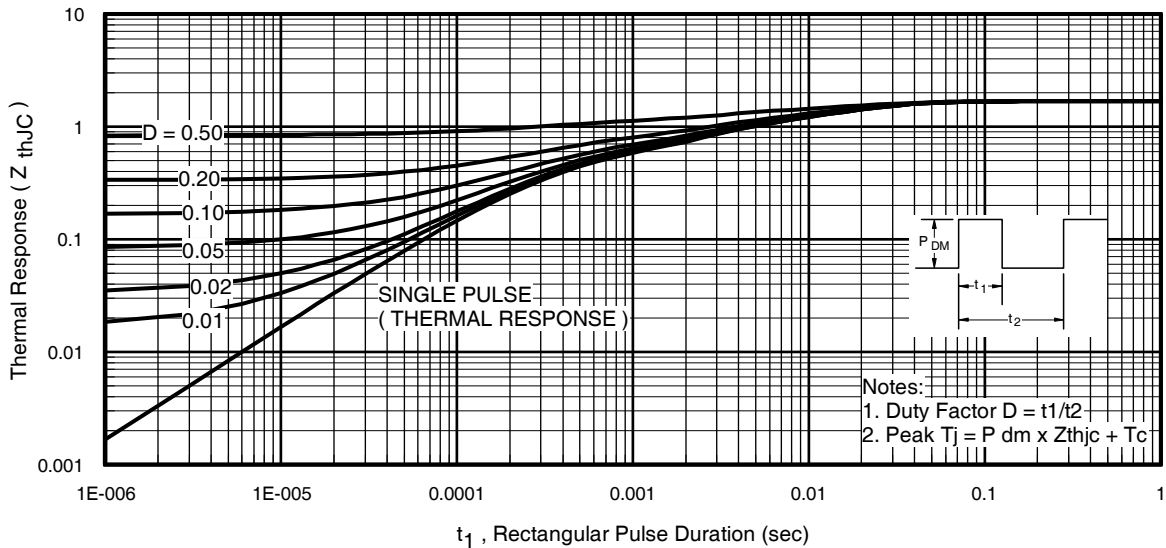


Fig 15. Maximum Effective Transient Thermal Impedance, Junction-to-Case

IRHYS67134CM, 2N7590T3

Pre-Irradiation

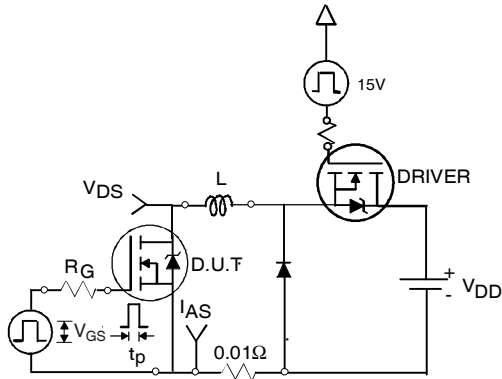


Fig 16a. Unclamped Inductive Test Circuit

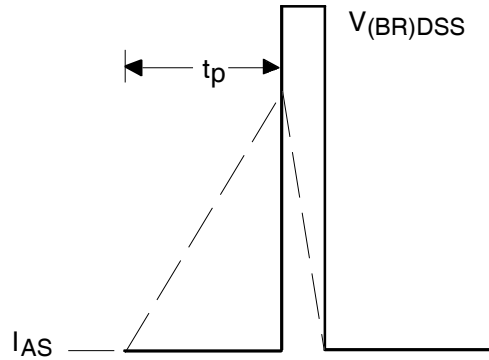


Fig 16b. Unclamped Inductive Waveforms

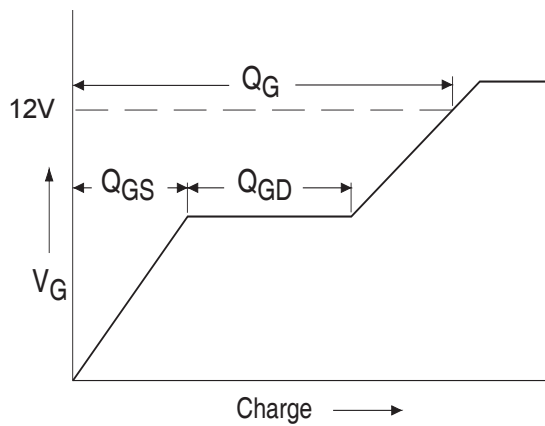


Fig 17a. Basic Gate Charge Waveform

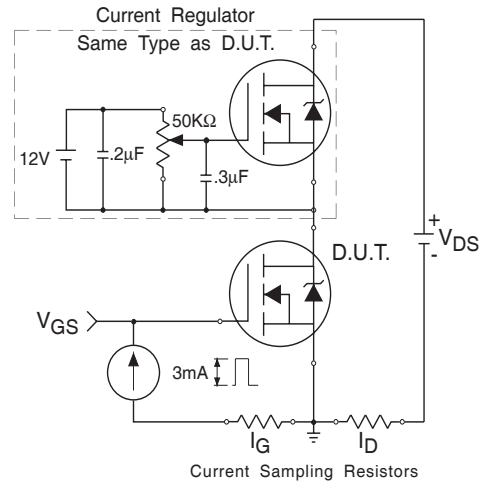


Fig 17b. Gate Charge Test Circuit

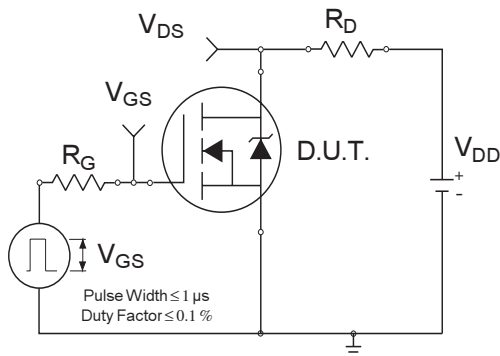


Fig 18a. Switching Time Test Circuit

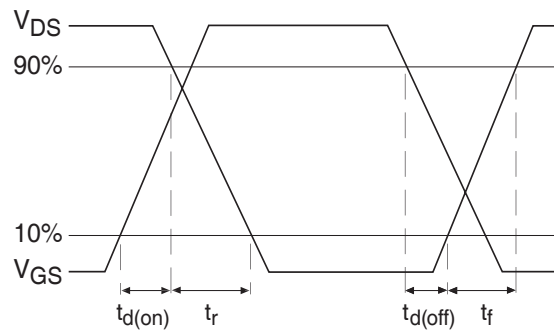


Fig 18b. Switching Time Waveforms

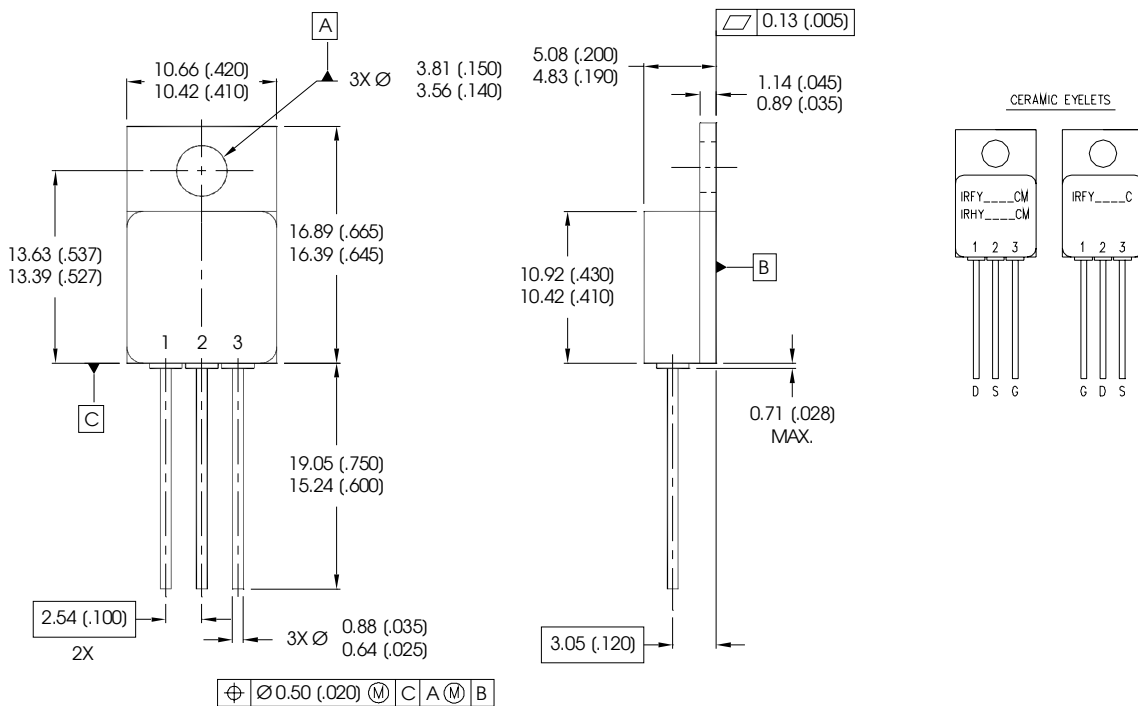
Pre-Irradiation

IRHYS67134CM, 2N7590T3

Footnotes:

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ② $V_{DD} = 25V$, starting $T_J = 25^\circ C$, $L = 0.37mH$
Peak $I_L = 19A$, $V_{GS} = 12V$
- ③ $I_{SD} \leq 19A$, $di/dt \leq 570A/\mu s$,
 $V_{DD} \leq 150V$, $T_J \leq 150^\circ C$
- ④ Pulse width $\leq 300 \mu s$; Duty Cycle $\leq 2\%$
- ⑤ **Total Dose Irradiation with VGS Bias.**
12 volt V_{GS} applied and $V_{DS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.
- ⑥ **Total Dose Irradiation with VDS Bias.**
120 volt V_{DS} applied and $V_{GS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.

Case Outline and Dimensions — Low-Ohmic TO-257AA



NOTES:

- 1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1994.
- 2. CONTROLLING DIMENSION: INCH.
- 3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
- 4. OUTLINE CONFORMS TO JEDEC OUTLINE TO-257AA

LEAD ASSIGNMENT

- 1 = DRAIN
- 2 = SOURCE
- 3 = GATE

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Data and specifications subject to change without notice. 01/2014